XBS306S17R-G



ETR1616-002a

Schottky Barrier Diode, 3A, 60V Type

■FEATURES

Forward Voltage : V_F=0.59V (TYP.)

Forward Current : $I_{F(AVE)}$ =3A Repetitive Peak Reverse Voltage : V_{RM} =60V

■APPLICATIONS

- Rectification
- Protection against reverse connection of battery

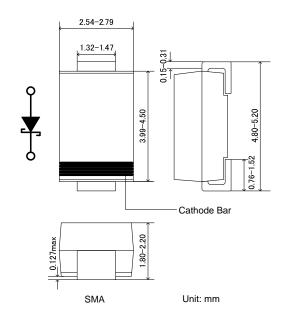
■ABSOLUTE MAXIMUM RATINGS

Ta=25°C

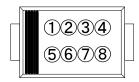
PARAMETER	SYMBOL	RATINGS	UNIT	
Repetitive Peak Reverse Voltage	Vrm	60	V	
Reverse Voltage (DC)	VR	60	V	
Forward Current (Average)	IF(AVE)	3	Α	
Non Continuous	IFSM	50	۸	
Forward Surge Current ^{*1}	IFSM	50	Α	
Junction Temperature	Tj	125	°C	
Storage Temperature Range	Tstg	-55~+150	°C	

^{*1:} Non continuous high amplitude 60Hz half-sine wave.

■ PACKAGING INFORMATION



■MARKING RULE



①23456: 306S17(Product Number)

: Assembly Lot Number

■PRODUCT NAME

PRODUCT NAME	DEVICE ORIENTATION		
XBS306S17 R-G	SMA (Halogen & Antimony free)		
XBS306S17 R	SMA		

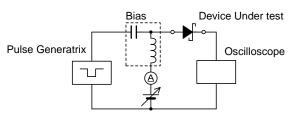
^{*} The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

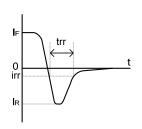
■ELECTRICAL CHARACTERISTICS

Ta=25°C

PARAMETER SYI	CVMPOL	MBOL TEST CONDITIONS	LIMITS			UNIT
	STIVIBUL		MIN.	TYP.	MAX.	UNII
Forward Voltage VF1 VF2	VF1	I _F =200 μ A	-	0.145	-	V
	VF2	I _F =3A	-	0.59	0.66	V
Reverse Current IR1 IR2	l _{R1}	V _R =30V	-	3	-	μΑ
	V _R =60V	-	9	300	μΑ	
Inter-Terminal Capacity	Ct	V _R =1V , f=1MHz	-	195	-	pF
Reverse Recovery Time*2	trr	I _F =I _R =10mA , irr=1mA	-	55	-	ns

^{*2 :} trr measurement circuit



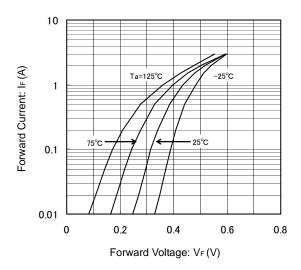


^{*} The device orientation is fixed in its embossed tape pocket.

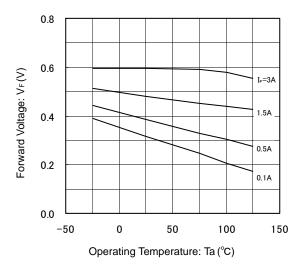
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■TYPICAL PERFORMANCE CHARACTERISTICS

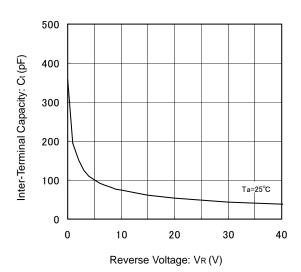
(1) Forward Current vs. Forward Voltage



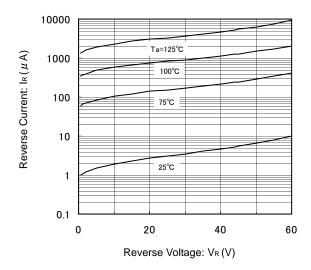
(3) Forward Voltage vs. Operating Temperature



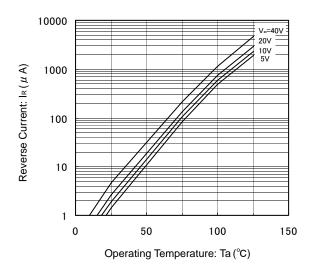
(5) Inter-Terminal Capacity vs. Reverse Voltage



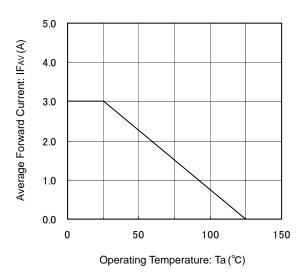
(2) Reverse Current vs. Reverse Voltage



(4) Reverse Current vs. Operating Temperature



(6) Average Forward Current vs. Operating Temperature



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